VS-150EBU04

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Vishay Semiconductors

Ultrafast Soft Recovery Diode, 150 A FRED Pt®



PRODUCT SUMMARY				
Package	PowerTab [®]			
I _{F(AV)}	150 A			
V _R	400 V			
V _F at I _F	0.9 V			
t _{rr} (typ.)	See recovery table			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC®-JESD 47
- PowerTab[®] package
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V _R		400	V
Continuous forward current	I _{F(AV)}	T _C = 104 °C	150	
Single pulse forward current	I _{FSM}	T _C = 25 °C	1500	А
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	300	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNIT
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 200 μA	400	-	-	
Forward voltage		I _F = 150 A	-	1.07	1.3	v
	V _F	I _F = 150 A, T _J = 175 °C	-	0.9	1.1	v
		I _F = 150 A, T _J = 125 °C	-	0.96	1.17	
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	50	μA
	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	4	mA
Junction capacitance	CT	C _T V _R = 400 V		100	-	pF
Series inductance	L _S Measured lead to lead 5 mm from package body - 3.5		-	nH		

Revision: 09-Jun-15 1 Document Number: 93003 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	-	60	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 150 A V _R = 200 V dI _F /dt = 200 A/μs	-	93	-	ns
		T _J = 125 °C		-	172	-	
Peak recovery current I _{RRM}	1	T _J = 25 °C		-	11	-	A
	IRRM	T _J = 125 °C		-	20	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	490	-	nC
		T _J = 125 °C		-	1740	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.35	K/W
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	r.∕ vv
Woight			-	-	5.02	g
Weight			-	0.18	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab [®]		150E	BU04	

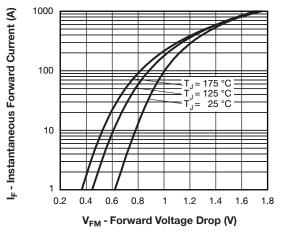


Fig. 1 - Maximum Forward Voltage Drop Characteristics

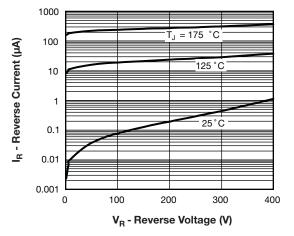


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage





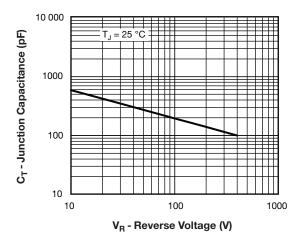


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

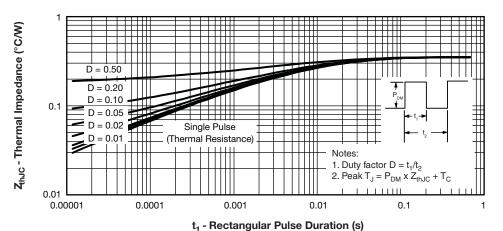
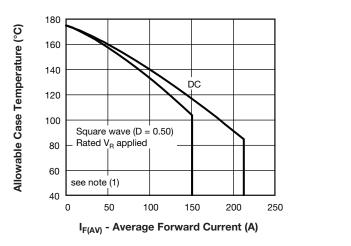
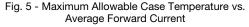


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





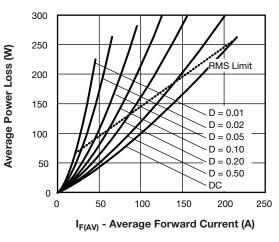


Fig. 6 - Forward Power Loss Characteristics

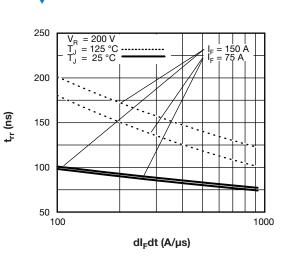
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

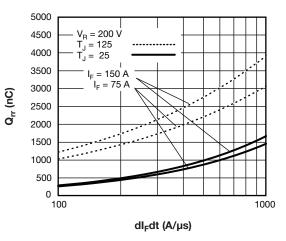


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

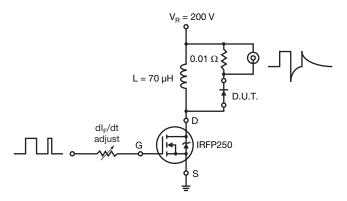
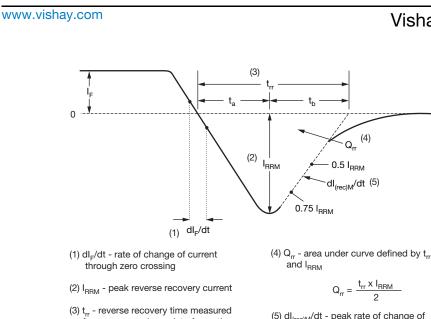


Fig. 9 - Reverse Recovery Parameter Test Circuit



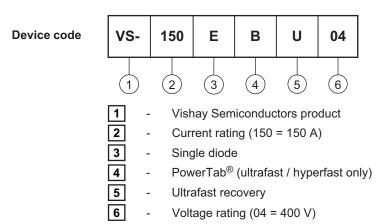


from zero crossing point of negative going I_F to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current.

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

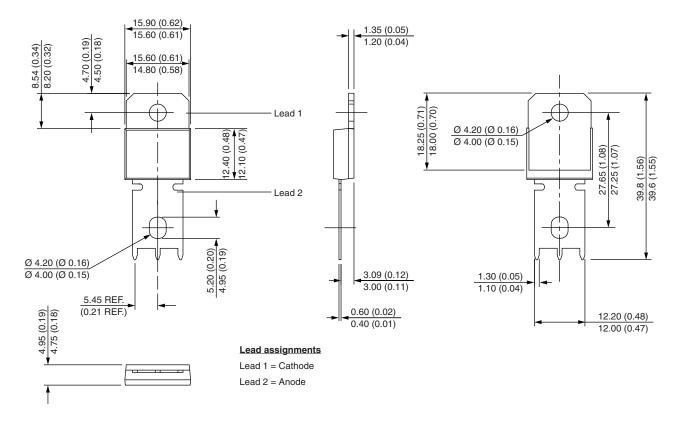


LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95240			
Part marking information	www.vishay.com/doc?95370			
Application note <u>www.vishay.com/doc?95179</u>				
SPICE model	www.vishay.com/doc?95623			



PowerTab[®]

DIMENSIONS in millimeters (inches)





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